

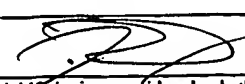
First Named Inventor	Kirk D. Prall	INFORMATION DISCLOSURE STATEMENT FORM PTO-1449
Serial No.	10/738,408	
Filing Date	December 16, 2003	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	8316	
Attorney Docket No.	400.249US01	
Title: NROM MEMORY CELL, MEMORY ARRAY, RELATED DEVICES AND METHODS		Sheet 1 of 7

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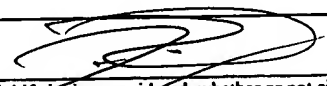
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Examiner Signature		Date Considered	12/21/05
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			